Single ion scattering contributions to the therm all conductivity of LiH oF $_4$ and LiY $_{96\%}$ H $o_{4\%}$ F $_4$

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W e have perform ed extensive zero- eld therm al conductivity m easurements on single crystal samples of LiH oF₄ and LiY $_{96\%}$ H $_{4\%}$ F₄ below 23 K. By comparing these data to a single ion scattering model, we have shown that the therm al conductivity of LiY $_{96\%}$ H $_{4\%}$ F₄ is dominated by simple single-ion scattering while that of LiH oF₄ shows additional contributions, possibly associated with collective spin excitations. No entirely satisfactory model, however, is available to explain the therm al conductivity of the ferrorm agnet.

I. IN TRODUCTION

LiHoF₄ has been the focus of num erous experim ental and theoretical studies ^{1,2}. The crystal eld constrains the angular momentum of the Ho³⁺ ions to lie strictly along the c-axis. Furtherm ore, the large Ho-Ho spacing greatly reduces the exchange term , m aking the system an excellent approximation to a model dipolar Ising ferrom agnet. The non-m agnetic ion Y³⁺ substitutes isostructurally and isoelectronically for Ho^{3+} , leading to dilute 3-d Ising systems. The latter are, for low magnetic ion concentrations, known to form a puzzling glassy system at low temperatures, whose signature is a narrowing distribution of barriers to relaxation as tem perature is low ered. One goal of m easuring therm al conductivity in these systems is to obtain coarse phonon spectroscopic data to probe the Ho³⁺ ion energy levels in the low-tem perature glass and ferrom agnet. Indeed, the LiH oF $_4$ and LiY $_{96\%}$ H o $_{4\%}$ F $_4$ characteristic hyper ne and magnetic energy level spectra are measured in the 100's of milli-Kelvins, making therm al phonons at tem peratures 1K an experimentally simple way to access the characteristic energies of the system (sim ple, that is, when compared to, e.g., millimeter photon spectroscopy). The central questions we ask are (a) whether low-tem perature collective excitations exist in the Ising ferrom agnet LiH oF $_4$ below $T_c = 1.53K$ and (b) whether the anom alous glassy behavior of the dilute system LiY 96% H 04% F4 is due to rearrangem ents of correlated spin clusters. In order to address these issues, we must analyze the data in such a way as to deconvolve the rather com plex single H o³⁺ ion contribution to the therm al resistance. W e will accomplish this via a detailed analysis of the crystal eld splittings and resulting single-ion excitations that cause phonon scattering.

II. SCATTERING MODEL

W e start with the general form of the therm alconductivity, , in terms of the phonon heat capacity, C (k), the m ean free path, l(k), and the the speed of sound, v(k), written as an integral over the phonon wave vector, k:

$$= C (k)v(k)l(k) d^{3}k:$$
 (1)

O ur initial approxim ations are to assume that the system is structurally isotropic with respect to k and that only acoustic phonons with a linear dispersion relation contribute at the experimental temperatures. We can then calculate the therm al conductivity in terms of an integral over the phonon frequency, !, as

$$= \frac{4}{v^2} C (!) l(!)!^2 d! :$$
 (2)

The specic heat, C (!) contribution from phonons with energy between ! and ! + d!, is the derivative of the m ean therm algenergy density of the lattice³,

C (!) d! =
$$\frac{d!}{8^{-3}} \frac{0}{0} \frac{h!}{e^{h! = k_B T} - 1}$$
: (3)

U sing equation 2, the therm al conductivity is now

$$= \frac{h^2}{2 v^2 k_B T^2} \int_{0}^{2} \frac{!^4 e^{h!} 1(!) d!}{(e^{h!} 1)^2} : \qquad (4)$$

Our task is to nd l(!), taking into account both single-ion magnetic scattering and scattering due to, e.g., crystalline defects. For reference, we reproduce in table II a synopsis³ of the ! dependence of various structural scattering mechanism s.

W e also assume the correctness of M athiesen's rule, i.e., that contributions the m ean free path are added reciprocally.

III. DETAILED SINGLE ION CALCULATION

The therm al resistance of an isolated Ho^{3+} ion may be num erically estimated from the electronic transition probabilities of the ions when they are excited by therm al phonons. We will not attempt here to calculate from rst

Type of scattering	l(!)/	(T)/
Externalboundaries	const:	T ³
G rain boundaries	const:	Т 3
Stacking faults	! 2	Т
Conduction electrons	!	T ²
Point defects	! 4	1=T
Um klapp processes	!	T ³ e ^{=T}

TABLE I: Table of the functional form of the mean free path, l, on !.

principles the electron-phonon coupling constants. Instead, we will use a sem i-phenom enologicalm odel to ascertain whether a single-ion scattering term can account for the observed therm alconductivity. The ${}^{5}I_{8}$ multiplet of the Ho^{3+} ions in LiHoF₄ is comprised of a ground state doublet followed by two singlets at about 9 and 39 K . The energy levels above these are of su ciently high energy that we can neglect them at the experim ental tem peratures. The ground state doublets are each split into 8 hyper ne sublevels which in turn m ay be split relative to each other due to a Zeem an interaction with an external or internal magnetic eld. The magnitude of the ground state magnetic splitting in the ferrom agnet was m easured by Battison et al.⁴. U sing an optical spectroscopic technique, they found it to be proportional to the magnetization (i.e., mean eld) with a maximum at zero tem perature equal to 2:6 cm 1 , or 3:7 K .

The energy levels are calculated by solving the eigenvalue problem for the ${}^{5}I_{8}$ single ion Hamiltonian. We follow the method described by Giraud et al.5. In the jJ;m ;I;ni basis, the H am iltonian can be approxim ated as the sum of the crystal eld, Zeem an, and hyper ne contributions,

$$H = H_{CF} + H_{Zee} + H_{hf}$$
: (5)

The crystal eld contribution is written in term of the Stevens' operators, O_1^m , and the crystal eld param eters, B_1^m . The resulting crystal eld Ham iltonian is

$$H_{CF} = B_{2}^{0}O_{2}^{0}$$

$$+ B_{4}^{0}O_{4}^{0} + B_{4}^{4}O_{4}^{4}$$

$$+ B_{6}^{0}O_{6}^{0} + B_{6}^{4}O_{6}^{4} ;$$
(6)

where , , and are ion specic coe cients calculated by Stevens⁶. For Ho^{3+} , = 1=450, = 1=30030, and = 1=3864861. (The general form for and can be found on page 253 of Hutchings⁷.) The crystal eld param eters, B_1^m , are given by G ifeism an et al. in reference⁸ and were measured through high resolution optical spectroscopy. Their values are: $B_2^0 = 273.9 \text{ K}$, $B_4^0 = 97.7 \text{ K}, B_6^0 = 6.5 \text{ K}, B_4^4 = 1289.1 \text{ K}, \text{ and}$ $B_6^4 = 631:6 K$.

O_1^m	in jJ;mibasis
0 2 0	$3J_{z}^{2}$ J (J + 1)
$O_4^{\ 0}$	$35J_z^4$ 30J (J + 1) J_z^2 + 25 J_z^2
	$6J (J + 1) + 3J^2 (J + 1)^2$
O_4^4	$\frac{1}{2}$ J ₊ ⁴ + J ⁴
0 6	$231J_z^6$ 315J (J + 1) J_z^4
	+ $735J_z^4$ + $105J^2$ (J + 1) ² J _z ²
	525J (J + 1) J_z^2 + 294 J_z^2
	$5J^{3}(J + 1)^{3} + 40J^{2}(J + 1)^{2}$
	60J (J + 1)
0 ⁴ ₆	$\frac{1}{4}$ 11J _z ² J (J + 1) 38 J ₊ ⁴ + J ⁴

TABLE II: Table of the Stevens' operators and equivalents.

 $11J_{z}^{2}$

 J_{+}^{4} + .T⁴

The Stevens' operators, O_1^m are given in reference 6 and 7 and the ones of interest here are summarized in table III.

The Zeem an contribution to the Ham iltonian is simply

$$H_{Zee} = g_{JB} \mathcal{J} \mathcal{H}$$
(7)

J(J + 1)

where the q-factor $q_J = 5=4$ for the J = 8 ground state, $_{\rm B}$ is the Bohrmagneton, and H is the magnetic eld due to applied external elds and the internal eld in the ferrom agnetic state. Due to the sym metry of the crystal, the internal magnetic eld due to ferrom agnetic order is directed along the (Ising) c axis. Therefore, in the absence of an external eld, and within the mean-eld approximation, we may write

$$H_{Zee} = g_{JB} \frac{H_0}{M_0} M (T) J_z;$$
 (8)

where M₀ is the saturation magnetization at zero tem perature, H $_0$ is the elective maximum internal eld at zero tem perature, and M (T) is the tem perature dependent magnetization. Note that this is the only term in the Ham iltonian where the tem perature enters into the calculation of the energy spectrum . (The therm albroadening of energy levels described below also depends on T.) The magnetization of LiH oF $_4$ is calculated from a t to the magnetization data measure in reference 9. The zero tem perature internal eld, H₀, is approxim ately 0:33 T which gives the correct splitting of 3:7 K at zero tem perature as m easured by Battison et al. 4. Note that since our sample geometry is a long bar along the c-axis, we do not apply a dem agnetization correction.

The hyper ne contribution m ay be written

$$H_{hf} = A_J \mathcal{J} \quad 1: \tag{9}$$

The coupling parameter A_J was found to be approximately 39 mK by Mennenga et al¹⁰ for LiHoF₄ from specic heat m easurem ents. M agarino et al¹¹ found approximately the same value for 2% Ho³⁺ diluted into $LiYF_4$ using electron param agnetic resonance.

For the Ho^{3+} ions in LiHoF₄ and LiY_{96%} $Ho_{4%}$ F₄, J = 8 and I = 7=2. Therefore, the Ham iltonian takes the form of a 136 136 Herm itian matrix. Num erical diagonalization gives the respective eigenvectors, which in tum allow the calculation of pertinent expectation values. Speci cally, it is in portant to know the expectation value of the z-com ponent of the nuclear angularm om entum, $hI_z i$, because transitions that change $hI_z i$ a large am ount are strongly suppressed. Figure 1 is a plot of the ground state doublet and the rst excited state eigenvalues plotted against the expectation values hJ_z i. The value of hIz i is written next to each point. The values for hIz i are uniform ly half integer as we would expect. Note that the scale of the hJz i axis on the top of the plot is one tenth that of the bottom to show the form of the excited state more clearly. Figure 2 is similar to gure 1 but with a magnetic eld turned on in the z direction. The eld used here is about 0:3 T, equal to that which would be generate internally by $LiH \circ F_4$ at zero tem perature. A swew ill discuss, only transitions between energy levels with I = 0 will be included in our computations.

There is one important note here about the energy eigenvalues in our particular case. The crystal eld param eters measured by G ifeism an et al.⁸ were measured through high resolution optical spectroscopy and they did not observe the 9.5 K excited state in their lum inescence spectra. Their param eters inserted into the calculation therfore predict that this unconstrained level sits at 14.5 K above the ground state doublet. Since this is the only state so e ected, we adjust our eigenvalues by subtracting 5 K from this state before using them in further calculations.

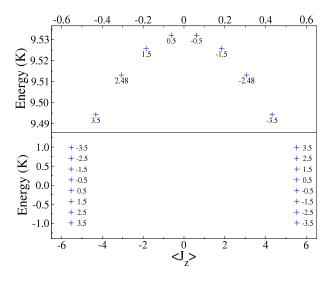


FIG.1: P lot of the energy eigenvalues arranged in term s of the $hJ_z\,i$ expectation values. The labels on the points are the $hI_z\,i$ expectation values. The bottom plot shows the ground state doublet, and the top plot is the $1^{\rm st}$ excited state.

Recall that the goal is to calculate a tem perature dependent m ean free path, 1(!), that is to be inserted in to the integral in equation 4. In the present case, we

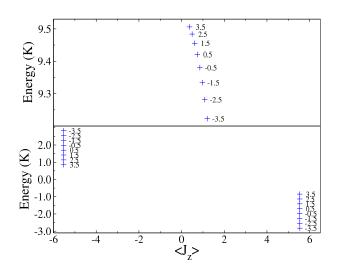


FIG.2: Similar to gure 1 but with magnetic splitting equal to what would occur in LiH oF $_4$ at 0 K. Note that the scale of the hJ_z i axis is the same in the top and bottom of the plot.

assume that there are only three scattering processes, giving us three independent l's to add. The rst is due to phonon scattering from the sample boundaries. This term is simply the geometrically averaged sample size, $l_{\rm br}$, and is independent of !. The second term is from scattering o of point defects, $l_{\rm pd}$, which gives a term proportional to 1=!⁴ (see table II). A swe shall see, this term is necessary to obtain agreement with the high tem – perature range of our data (though higher dimensional defects might also su ce, we assume point defects for simplicity). The last process is due to the non-trivial scattering from the Ho³⁺ ions, $l_{\rm ion}$. Therefore,

$$l = \frac{1}{\frac{1}{l_{br}} + \frac{1}{l_{pd}} + \frac{1}{l_{ion}}};$$
 (10)

We choose to write the mean free path due to the single ion scattering process as $l_{ion} = l_{m in} = P_{scatt}$. The scale factor $l_{n in}$ is similar to the minimum distance that a phonon can go without running into a Ho^{3+} ion, and P_{scatt} is the probability that the phonon will scatter o of that ion. We de ne l_{pd} $\frac{1}{1^4}$, and will use as a tting parameter. Our complete expression for the mean free path is then

$$l(!) = \frac{1}{\frac{1}{l_{br}} + \frac{!}{4} + \frac{P_{scatt}(!,T)}{l_{m} in}};$$
 (11)

A fler computing the energy level spectrum at a particular tem perature, we calculate the partition function which is obtained by sim ply sum m ing over each level, E $_{\rm i}$, integrated over the level density, D $_{\rm i}$ (),

$$Z = \begin{bmatrix} X & Z_{1} \\ & e & D_{i}()d : \\ & & i \end{bmatrix}$$
(12)

W e assume that the individual energy levels are thermally broadened (due to crystal eld uctuations from therm almotion of the atom ic neighbors of the Ho^{3+} ions in the lattice) with a Gaussian energy distribution. For sim plicity, we further assume that all of the levels are have the same width, E, resulting in the following energy density function,

$$D_{i}() = \frac{1}{E^{p-e}} e^{\frac{(E_{i})^{2}}{E^{2}}}:$$
 (13)

Our partition function now becomes

$$Z = e^{\frac{2}{4} E^2} X e^{E_i}$$
 (14)

The scattering probability, P_{scatt} (E_P;T), is a function of the phonon energy, $E_P = h!$, and the tem perature of the system, T. We calculate it by perform ing a double sum over all the energy levels, calculating the scattering probabilities between each pair.

$$P_{\text{scatt}}(\mathbf{E}_{P};\mathbf{T}) = h\mathbf{I}_{z}^{(i)}\mathbf{i} h\mathbf{I}_{z}^{(j)}\mathbf{i} \quad (15)$$

$$X \quad \mathbf{Z}_{1} \quad \mathbf{e} \quad \mathbf{D}_{ij}()\mathbf{d}$$

$$i_{j}\mathbf{I}_{1} \quad \mathbf{e} \quad \mathbf{D}_{ji}()\mathbf{d};$$

where $D_{ij}() = D_i()D_j(+ E_P)$ and $D_{ji}() = D_j()D_i(E_P)$. This particular form takes into account stimulated emission from the higher level to the lower one as well as the direct excitation of the ion. The delta function allows for excitations only between levels that have the same nuclear angularmomentum expectation values (see Fig's 1 and 2). Slightly decreasing this selectivity, say by allowing $hI_z^{(i)}i hI_z^{(j)}i$ to vary by one or two, makes little di erence to the current model except at the lowest temperatures (< 100 m K). U sing the level density mentioned above, the scattering probability is found to be

$$P_{\text{scatt}} (E_{P}; T) = \frac{1}{Z} e^{\frac{1}{B}^{2} - \frac{2}{E} - 2}$$
(16)

$$n = e^{E_{P} - 2} e^{-E_{P} - 2}$$

$$X = \frac{(E_{1} - E_{1} + E_{P})^{2}}{2 - E^{2}} e^{-\frac{1}{2} - 2} (E_{1} + E_{1})$$

$$i; j$$

$$hI_{z}^{(i)} i hI_{z}^{(j)} i :$$

The energy level width, E, requires attention here. The therm all energy due to deform ation of the lattice is essentially

$$E_{T} = k_{b}T = \frac{1}{2}C_{0}^{2};$$
 (17)

where C_0 is an averaged elastic constant, and is an averaged strain. For sm all lattice deform ations changes in the crystal eld energy are therefore proportional to the strain,

$$E_{CF}$$
 / : (18)

 $\ensuremath{\mathbb{W}}$ e collect the constants, and designate the thermal broadening as

$$E = A \stackrel{p}{T} :$$
 (19)

with A as a tting parameter.

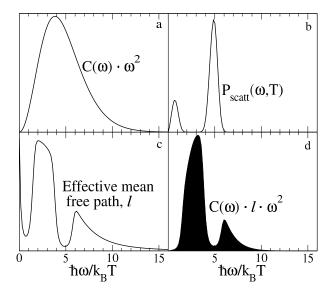


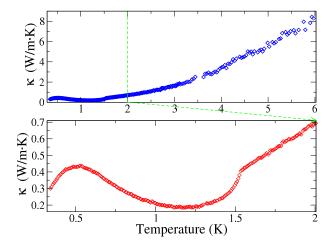
FIG.3: P lots of the contributions to the heat capacity calculation for T = 2 K. The various panels are described in the text.

The therm al conductivity is calculated at each tem – perature by the following procedure. First the various tem perature dependent parameters (internal eld for LiH oF₄ and the broadening parameter A) are set and the H am iltonian eigenvalue problem is solved. The integral in equation 4 is computed by inserting the mean free path, 1(!), from equation 11. The scattering probability is then calculated at each point in the integral using equation 16 where $E_P = h!$.

We have used an integration cut-o of $! = 16k_B T = h$, which is quite su cient as seen in Figure 3. Panela is the heat capacity part of the integrand which essentially vanishes for higher frequencies. Panelb is the scattering probability from equation 16, and panel c is l(!) from equation 11. The last panel, d, is the integrand to equation 4, so the area of the lled portion represents the total therm al conductivity at this tem perature. The effect of transitions between Ho^{3+} levels is quite apparent in the mean free path data, e ectively removing speci c frequency bands from the therm al conductivity integral.

Therm al conductivity was measured by the standard gradient m ethod using a heater and two therm om eters. Our heaters were 200 metal lm on Kapton strain gauges and the therm on eters used were 1 k to 10 kRuO₂ surface mount resistors, depending on the tem perature range of interest. Copper bars approxim ately 150 m thick were silver epoxied to the sample dividing it approximately into thirds. These bars de ned the distance over which the temperature gradient, T = T_1 , was measured. The heaters were wired with T_2 superconducting NbTi wires to eliminate ohmic heating and to minimize heat leaks, while thin Evanohm wires were used on the thermometers. To check for therm al leakage through the wires, the measurem ent of $LiY_{96\%}Ho_{4\%}F_4$ was repeated with the wires doubled in length. The results of the therm al conductivity between the two sets of measurements were within the noise of either experiment. Our two samples (pure and dilute) were optically oriented and cut such that the long length was along the c axis. The pure $LiHoF_4$ was 1:46 1:56 5:4 mm³. This gives a cross section of 0:0228 cm². The distance, L, between the therm om eters was0:22 cm . The 11:7 mg dilute LiY 96% H 04% F4 sample was 0:93 0:75 4:7 m m³, but slightly trapezoidal. The e ective cross section was calculated by using measurements from a digital photograph of the sample. The nal value used was A = 0.0066 cm². The distance between therm om eters for this sample was also 0:22 cm. Most experim ents were conducted in a ³H e cryostat. D at a below 310m K were obtained in a helium dilution refrigerator.

V. EXPERIMENTAL RESULTS



A. Pure LiHoF₄

FIG. 4: M easured therm al conductivity, , for LiH oF $_4$. The bottom panel is a m agni cation of the top to better illustrate the structure below the Curie Tem perature, $T_{\rm C}$.

The accumulated data for a number of experiments are plotted in gure 4. The top panel is the entire range of data obtained, and the bottom is a magni cation of data below 2 K . One can easily see the ferrom agnetic transition on this plot at 1:54 K . O ne interpretation of the overall structure of the data is as follows; as we go down in tem perature, the therm alconductivity decreases due to the T³ term in the speci cheat. At this point, the vast majority of phonon-driven transitions are between the hyper ne ground state sublevels. W hen we reach $T_{\rm C}$, the ground states start Zeem an splitting, and there are a number of new transition possibilities opened up, so the conductivity drops rapidly. Note that the peak in C(!) in gure 3 occurs at approximately $! = 4k_bT = h$. This implies that at $T_{\rm C}$, about 1:5 K , the majority of phonons have energies around 6 K . How ever, just above $T_{\rm C}$, the Ho³⁺ energy spectrum looks like that shown in gure 1, where there are no scattering possibilities for phonons between about 2 K and about 8.5 K. Below T_C, the excluded tem perature region quickly shrinks due to the splitting, and simultaneously, the peak of the phonon spectrum decreases. At about 1:2 K, the ground states have split enough that transitions are suppressed and the conductivity starts increasing. Eventually, this rise is expected to be countered by the T³ factor from having a sample of nite size. W hile this qualitative explanation was the primary motivation to develop a single ion model of the therm al conductivity we shall see that this picture is not su cient to explain all of the data.

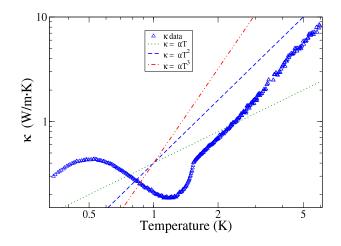


FIG.5: log-log plot of for LiH of $_4$ along with some lines of T n for comparison with table II.

Figure 5 shows the whole range of data on a log-log plot, along with lines proportional to T, T², and T³. Recall from table II the various structural scattering processes that can contribute to the therm al conductivity. As one can see, the data do not follow any one of these power laws over any signi cant tem perature range. We did not take m easurem ents of the pure LiH oF₄ in the dilution refrigerator, so we can not see the approach to T³ in the low tem perature lim it.

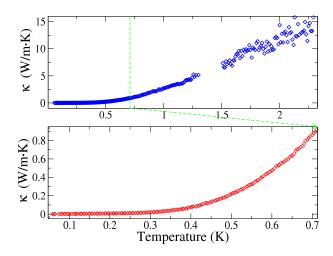


FIG.6: M easured for LiY $_{96\$}$ H $_{4\$}$ F $_4$. The bottom panel is a magni ed view of the top.

B. Dilute LiY 96% Ho4% F4

We have again plotted our data in two temperature ranges in gure 6. This plot is not very illuminating by itself since it goes so quickly and smoothly to zero. There is no ferrom agnetic transition, so there are no sharp structures as there are for LiHoF₄. (The gap in the data between 1:3 K and 1:5 K is due to T-control issues in the ³He cryostat.) As in the previous section, the data becomes increasingly noisy at higher temperatures due to the reduced sensitivity of the therm on eters and the rapidly increasing them alconductivity. Note that at 2 K the therm alconductivity of LiY_{96%} Ho_{4%} F₄ is about 10 times that of LiHoF₄, but slightly smaller at 0:5 K.

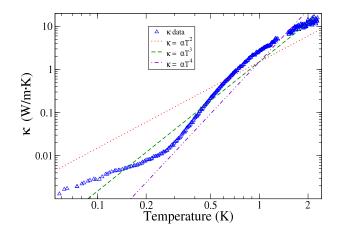


FIG.7: log-log plot of for LiY $_{96\$}$ H $o_{4\$}$ F $_4$ along with some T n lines for comparison.

Figure 7 is a plot of log() versus log(T) to check for regions where the therm al conductivity is dom inated by a single power law. It appears that at the lowest tem – peratures the data may be approaching T³, but going to lower tem peratures would be necessary to con m this.

M ore importantly, the log plot brings out structures that must be reproduced by our single-ion model if it is to describe the data.

VI. ANALYSIS

Our goal is to nd a set of param eters that provide the best t for both our LiH oF 4 and LiY 96% H 04% F 4 data simultaneously. Fitting parameters include , which determ ines the contribution from point defect scattering, and $l_{m \ in}$, which determ ines the size of the contribution from the Ho³⁺ ion scattering. P_{scatt} also contains a param eter that can be varied, as does the the therm all broadening, Eq. 19. Since A is a single ion property, it should be independent of the concentration of the Ho^{3+} ions. Sim ilarly, $l_{m in}$ should be proportional to the inverse of the cube root of the concentration, xing its relative value. The e ective mean free path due to the nite size of the sam ple, lpr, is calculated from the sam ple dim ensions and is xed. We take A_J from equation 9 to be a constant, 38:6 m K , since this value has been m easured and published using at least two di erent m ethods^{10,11}. A s m en-0:33T from equation 8 was indirectly, and tioned, H₀ som ew hat im precisely, m easured by Battison et al⁴.

We will rst discuss the dilute glassy system LiY $_{96\$}\,\text{Ho}_{4\$}\,\text{F}_4$.

A. Dilute LiY $_{96\$}$ H $o_{4\$}$ F $_4$

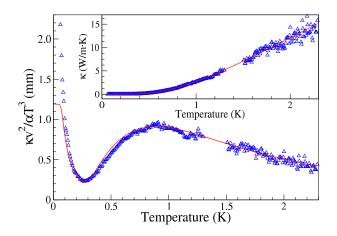


FIG.8:Plotof $v^2=$ T 3 and best tfor L1 $\!Y_{96\,\$}$ H $o_{4\,\$}$ F $_4$. Inset is .

Figure 8 is a plot of and $v^2 = T^3$ for LiY $_{96\$} H o_{4\$} F_4$ along with the best model t. Here,

$$=\frac{2^{2}}{15}\frac{k_{b}^{4}}{h^{3}}$$
 (20)

which gives us $=T^3$ roughly in units of the mean free path (the equivalence would be exact of l did not depend on !). As we can see, the t is quite good with this parameter set. The best t parameters are A = 0.45 0.03 K $^{1=2}$, $l_{\rm m \ in}$ = 38 1 m, and = 15 2 m K. The uncertainties were estimated by varying the individual parameters to obtain the same m inim um 2 , and do not react any correlations between the parameters. As we can see, the scattering due to point defects is a fairly small contribution. For example, a 1 K phonon will have a mean free path, due to this process, of about 15 meters. Only for phonons with energies greater than about 12 K does the mean free path to become smaller than the physical size of the sample. Because of this, the initial tting was done with = 1, after which was adjusted

to m in im ize the 2 .

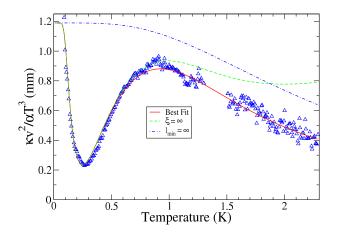


FIG.9: Plot of $v^2 = T^3$ and variations on the best t for LiY_{96%} Ho_{4%} F₄. The parameters are described in the text.

Figure 9 dem onstrates how each parameter e ects the model. Unless noted, all lines shown here use the \best t" parameters. The dashed line has the point defect scattering turned o by setting = 1 . Note that this line follows the best t line fairly well for temperatures below the peak at 900 m K , and is identical for temperatures the e ect of turning o the Ho³⁺ single ion scattering process by by setting $l_{m in} = 1$. If we turned o the point defect scattering at the same time, we would obtain a horizontal line at $v^2 = T^3 = l_{\rm br} = 1.19$ mm. From this, we see that the single ion process alone is responsible for the scattering causes a turn-over in the data to produce the peak at 900 m K .

In the very low temperature region, less than 80 mK, the model demonstrates a attening behavior that is not present in the data. This is due to the value of $l_{\rm br}$, since it sets the overall maximum mean free path. Interestingly, increasing $l_{\rm br}$ beyond its physical value does not improve the overall model, as this e ectively scales the entire t. There currently is no parameter set in with this model that reproduces the T < 80 mK region while retaining agreement with the rest of the data set. One explanation for this could be related to the surface condition of the sample. At very low temperatures, phonons

will have an increasing wavelength, which will eventually become larger than the surface roughness. When this occurs, the boundary scattering becomes specular and the elective mean free path due to the nite size of the sample increases. This would result in a rapid uptum of $=T^3$ when this limit is reached, consistent with our measurements.

We believe that this single ion model describes the thermal conductivity of LiY_{96%} Ho_{4%} F₄ fairly well below 2.5 K, and demonstrates the relative in portance of scattering from point defects. We see no sign of the \cluster glass" proposed by Reich et. al^2 . They observed narrowing in the magnetic susceptibility with decreasing tem peratures between 300 m K and 150 m K, but we see no signs of collective behavior in this tem perature range.

B. Pure LiHoF4

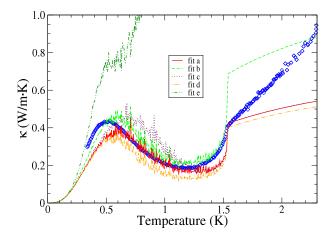


FIG.10: Plot of $v^2 = T^3$ and three ts for LiHoF4. Param – eters are described in the text.

We now move to the ferrom agnet $LiHoF_4$. Because A should be independent of the concentration of the Ho^{3+} ions, and $l_{m in}$ should be proportional to the inverse of the cube root of the concentration, we will start with A = 0.45 K $^{1=2}$, $l_{m in} = {}^{3^{P}} \overline{4\%}$ 38 = 13 m, and = 15 m K⁴. from the analysis of LiY $_{96\%}$ H $o_{4\%}$ F $_4$. W e also turn on the Zeeman splitting by setting H_0 from equation 8 to 0:33 T. Figure 10 is a plot of $v^2 = T^3$ versus temperature for $LiHoF_4$ with three lines from our model. Note that the vertical axis is on a log scale so that the structure of the ferrom agnetic transition can be seen. The solid line is our \best t" with the above param eters. The dashed line uses the same param eters except for = 1 to see the e ect of turning o the point defect scattering. The dot-dashed line has $l_{m in} = 1$ to demonstrate the e ect of turning o the Ho^{3+} single ion scattering contribution (the individual contributions are more protably viewed using the color gure available online). As we can clearly see, the \best t" is poor. Furtherm ore, no am ount of adjustm ent of the

param eters appears to yield signi cantly better agreem ent. W e do, how ever, see som e qualitative successes with this model of LiHoF₄. The behavior immediately below the Curie tem perature is generally what we predicted from section V A and we see a reasonably accurate rollo in $=T^3$ at the low est tem peratures. One possibility is that there are one or more additional scattering mechanisms needed in the model. For example, below the Curie temperature, domain formation could introduce a tem perature dependent grain boundary-like scattering process. However, this would have no e ect above $T_{\rm C}$, where the deviation from the t is most pronounced. (Of course, it is possible that di culties present below T_C in the model result in best-t deviations above the Curie point.) The second, and potentially most interesting possibility is that phonon-excited spatially correlated spin-ips account for the enhanced scattering. Note that, unlike isotropic or nearly isotropic system s, conventional spin-waves are not expected in an ensemble of Ising spins. Indeed, the nature of (potentially collective) magnetic excitations above and below $T_{\rm C}$ in this dipolar-coupled system are unclear, as is the question of whether such magnetic scattering could account for the behavior we observe. Again, one would naively believe such e ects to strongly dominate below $T_{\rm C}$. At higher temperature it is unclear what multi-spin excitations are available to couple to the phonon current.

In conclusion, a detailed sem i-phenom enologicalm odel of single-ion phonon scattering processes is in excellent agreement with them al conductivity data on dilute LiY $_{96\%}$ H $_{4\%}$ F₄, with no evident signature of low – energy collective excitations involving random spin clusters. Sim ilar data on the pure ferrom agnetic system LiH oF₄, how ever, are not in quantitative agreement with the independent ion theory and will presum ably require a study of collective e ects in this dipolar Ising system .

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